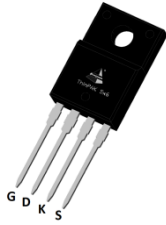




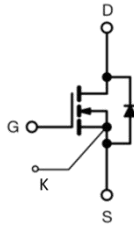
## N-channel Power MOSFET

## PRODUCT SUMMARY

$V_{DS}$ (V) at $T_J$ max.	700	
$R_{DS(on)}$ max. at 25°C (mΩ)	$V_{GS}=10V$	75
$Q_g$ max. (nC)	90	
$Q_{gs}$ (nC)	17	
$Q_{gd}$ (nC)	30	
Configuration	single	



TO-220F 4PIN



Schematic diagram

## Features

- Kelvin connection (Pin K) for reduced gate noise
- New Technology For High Voltage Device
- $ID=46A(V_{GS}=10V)$
- Ultra Low Gate Charge
- Improved  $dv/dt$  Capability
- RoHS compliant

Please note: Pin SS and S are not exchangeable, Their exchange might lead to malfunction.

## Applications

- Switching Mode Power Supplies (SMPS)
- Server and Telecom Power Supplies
- Welding & Battery Chargers
- Solar (PV Inverters)
- AC/DC Bridge Circuits

## ORDERING INFORMATION

Device	SPU65R75G
Device Package	TO-220F 4PIN
Marking	65R75G

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ C$ , unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain to Source Voltage	$V_{DSS}$	650	V
Continuous Drain Current (@ $T_C=25^\circ C$ )	$I_D$	46 <sup>(1)</sup>	A
Continuous Drain Current (@ $T_C=100^\circ C$ )		28 <sup>(1)</sup>	A
Drain current pulsed <sup>(2)</sup>	$I_{DM}$	138 <sup>(1)</sup>	A
Gate to Source Voltage	$V_{GS}$	$\pm 30$	V
Single pulsed Avalanche Energy <sup>(3)</sup>	$E_{AS}$	1300	mJ
MOSFET $dv/dt$ ruggedness (@ $V_{DS}=0\sim 400V$ )	$dv/dt$	25	V/ns
Peak diode Recovery $dv/dt$ <sup>(4)</sup>	$dv/dt$	15	V/ns
Total power dissipation (@ $T_C=25^\circ C$ )	$P_D$	35.7	W
Derating Factor above 25°C		0.28	W/°C
Operating Junction Temperature & Storage Temperature	$T_{STG}, T_J$	-55 to + 150	°C
Maximum lead temperature for soldering purpose	$T_L$	260	°C

## Notes

1. Drain current is limited by maximum junction temperature.
2. Repetitive rating : pulse width limited by junction temperature.
3.  $L = 37.5mH, I_{AS} = 8A, V_{DD} = 50V, R_G = 25\Omega$ , Starting at  $T_J = 25^\circ C$
4.  $I_{SD} \leq I_D, di/dt = 100A/us, V_{DD} \leq BV_{DSS}$ , Starting at  $T_J = 25^\circ C$
5. Mounting consideration for TO220 Fullpack:  
M3 screw plus flat washer is suggested, free of burr between devices and contact area, the devices are to be mounted to a hole not larger than 3.6mm in contact diameter (chamfer included).



THERMAL CHARACTERISTICS			
Parameter	Symbol	Value	Unit
Thermal resistance, Junction to case	$R_{thjc}$	3.5	°C/W
Thermal resistance, Junction to ambient	$R_{thja}$	38	°C/W

ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise specified )						
Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
Drain to source breakdown voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	650	--	--	V
Breakdown voltage temperature coefficient	$\Delta BV_{DSS} / \Delta T_J$	$I_D=250\mu A$ , referenced to $25^\circ\text{C}$	--	0.38	--	V/°C
Drain to source leakage current	$I_{DSS}$	$V_{DS}=600V, V_{GS}=0V$	--	--	1	$\mu A$
		$V_{DS}=480V, T_C=125^\circ\text{C}$	--	120	--	$\mu A$
Gate to source leakage current, forward	$I_{GSS}$	$V_{GS}=30V, V_{DS}=0V$	--	--	100	nA
Gate to source leakage current, reverse		$V_{GS}=-30V, V_{DS}=0V$	--	--	-100	nA
<b>On Characteristics</b>						
Gate threshold voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	--	4.5	V
Drain to source on state resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=23A$	--	62	75	m $\Omega$
Forward Transconductance	$G_{fs}$	$V_{DS} = 30 V, I_D = 23A$	--	32	--	S
Gate Resistance	$R_g$	$V_{DS} = 0 V$		1.1		$\Omega$
<b>Dynamic Characteristics</b>						
Input capacitance	$C_{iss}$	$V_{GS}=0V, V_{DS}=200V, f=1\text{MHz}$	--	3220	--	pF
Output capacitance	$C_{oss}$		--	122	--	
Reverse transfer capacitance	$C_{rss}$		--	3	--	
Turn on delay time	$t_{d(on)}$	$V_{DS}=300V, I_D=23A, R_G=25\Omega$	--	32	--	ns
Rising time	$t_r$		--	72	--	
Turn off delay time	$t_{d(off)}$		--	110	--	
Fall time	$t_f$		--	67	--	
Total gate charge	$Q_g$	$V_{DS}=480V, V_{GS}=10V, I_D=23A$	--	72	90	nC
Gate-source charge	$Q_{gs}$		--	17	--	
Gate-drain charge	$Q_{gd}$		--	30	--	

SOURCE TO DRAIN DIODE RATINGS CHARACTERISTICS						
Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous source current	$I_S$	Integral reverse p-n Junction diode in the MOSFET	--	--	46	A
Pulsed source current	$I_{SM}$		--	--	138	A
Diode forward voltage drop.	$V_{SD}$	$I_S=23A, V_{GS}=0V$	--	0.9	1.2	V
Reverse recovery time	$T_{rr}$	$I_S=23A, V_{GS}=0V, di_f/dt=100A/\mu s$	--	420	--	ns
Reverse recovery Charge	$Q_{rr}$		--	7.2	--	$\mu C$



Fig1. Output characteristics

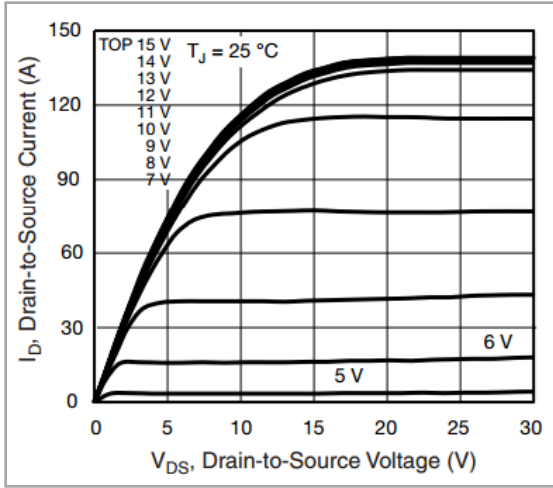


Fig2. - Maximum Drain Current vs. Case Temperature

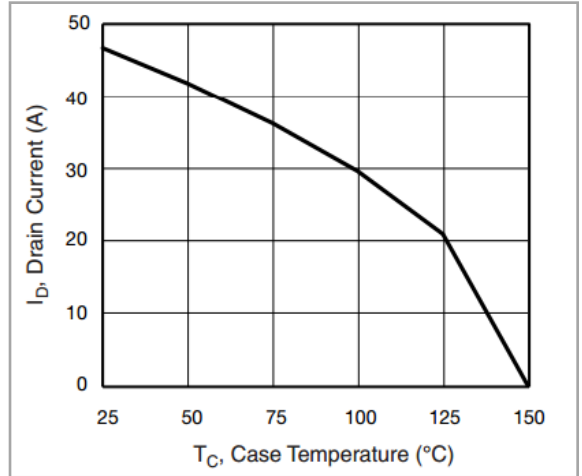


Fig3. Gate charge characteristics

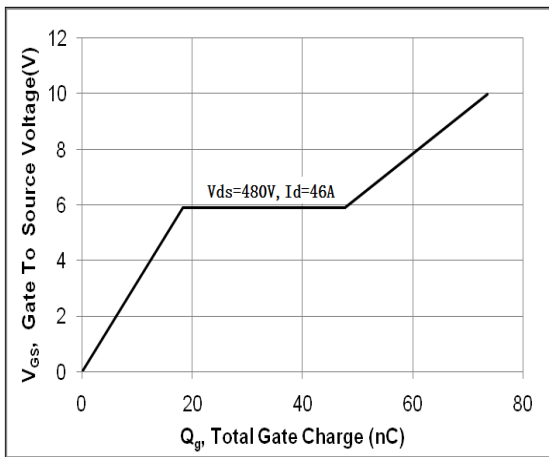


Fig 4. Capacitance Characteristics

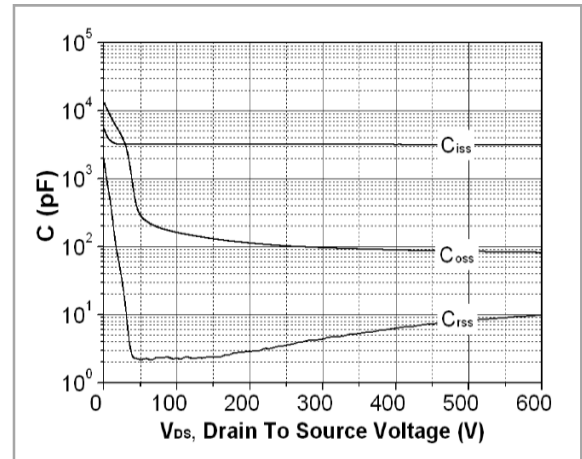


Fig 5.  $R_{DS(ON)}$  vs junction temperature

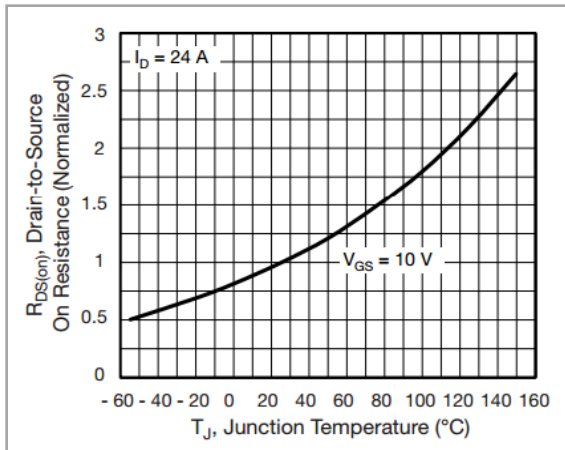


Fig 6. - Temperature vs. Drain-to-Source Voltage

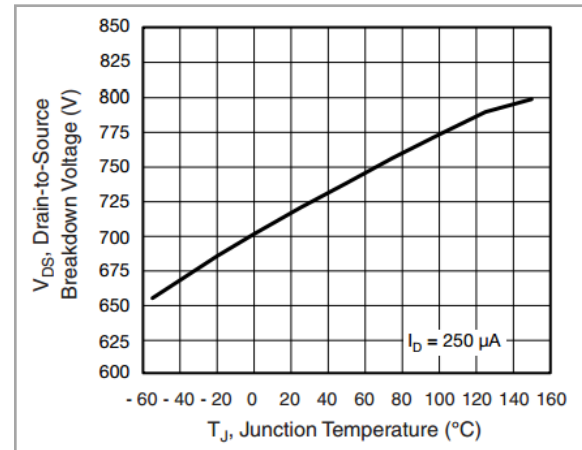


Fig 7 . Safe operating area

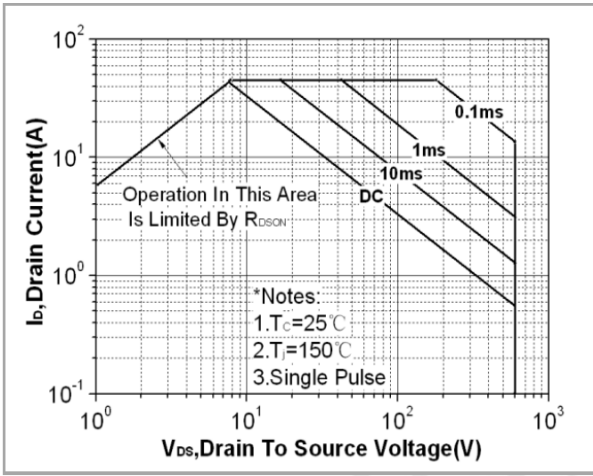


Fig 8. Forward characteristics of reverse diode

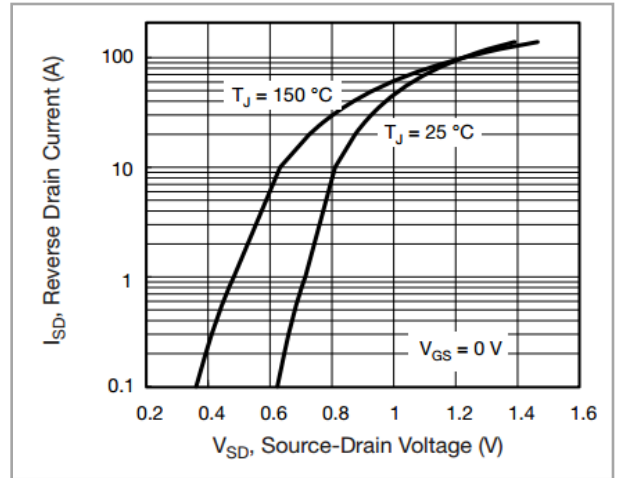


Fig 9 . Transient thermal impedance

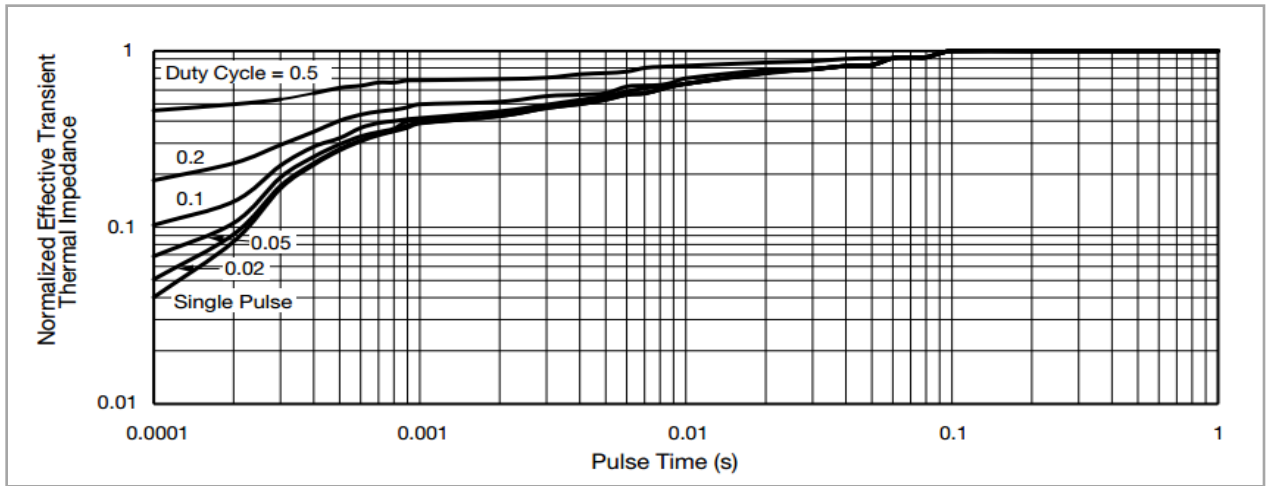


Fig 10. Gate charge test circuit & waveform

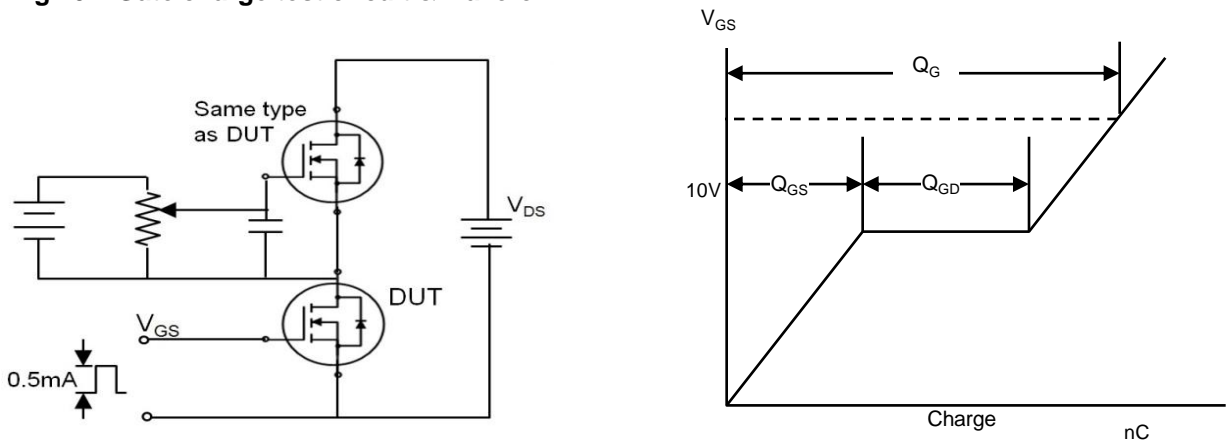


Fig 11. Switching time test circuit & waveform

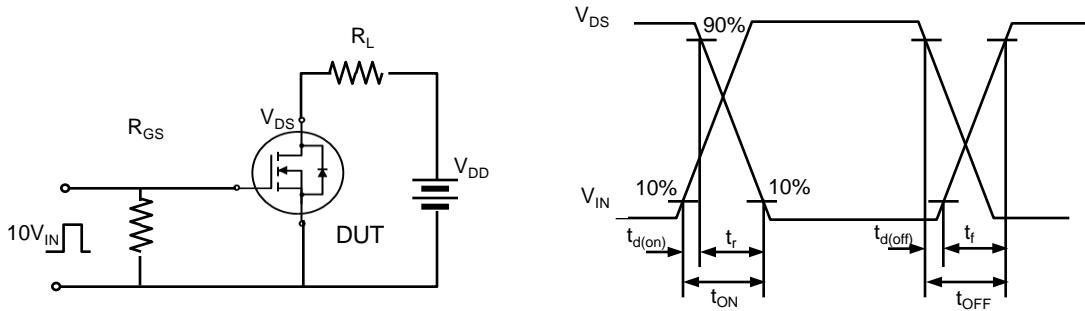


Fig 12. Unclamped Inductive switching test circuit & waveform

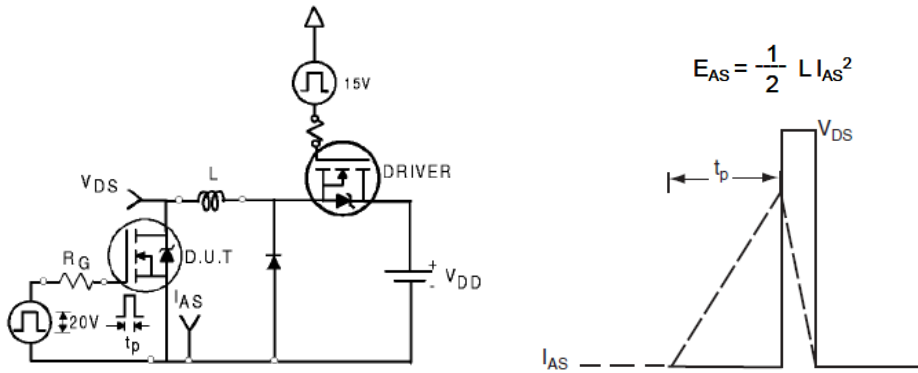
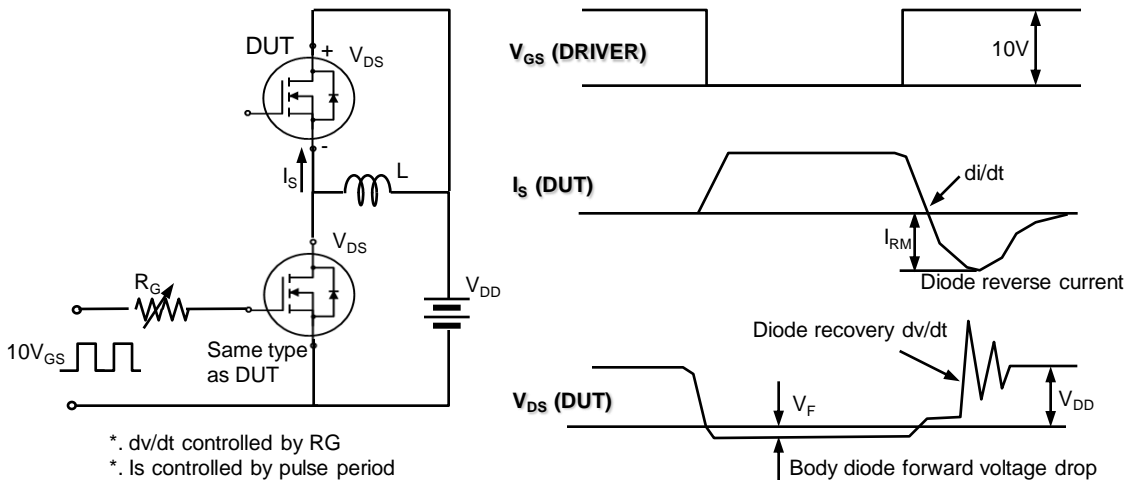
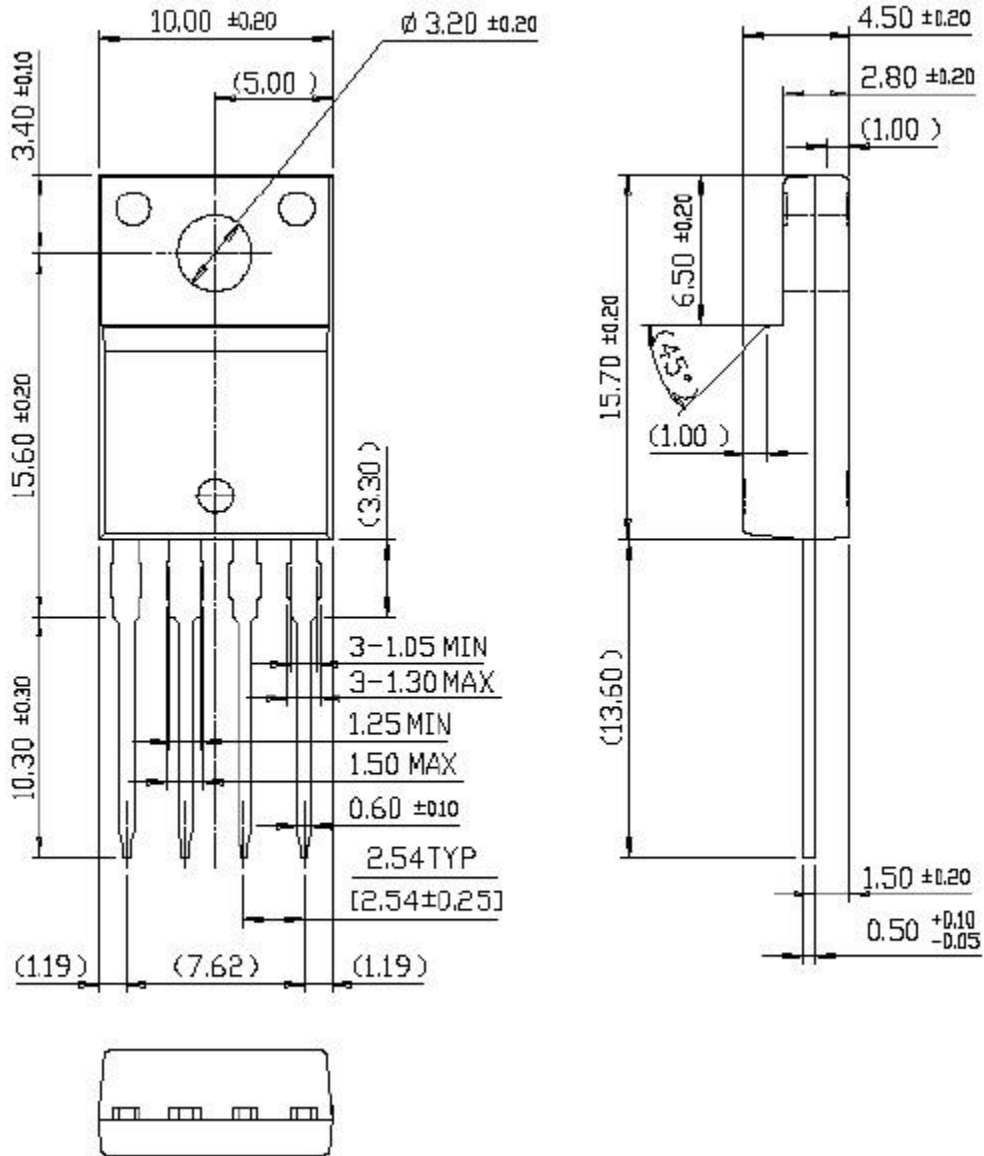


Fig 13. Peak diode recovery dv/dt test circuit & waveform





Package Outline Drawing ---- TO-220F 4PIN





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